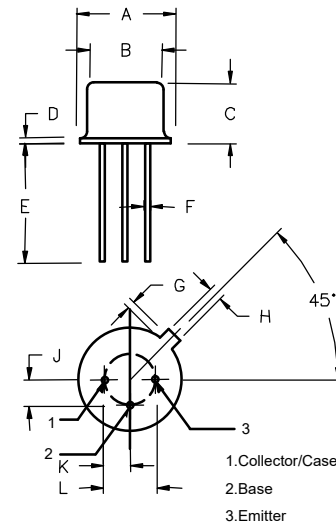


DESCRIPTION

A silicon NPN transistor, designed for VHF and UHF equipment. Applications include amplifier, pre-driver, driver, and output stages.

FEATURES

- Silicon NPN, TO-39 packaged VHF/UHF Transistor
- $f_t=1.0$ Ghz (typ) @ 400MHz, 28V, $I_c=50$ mA
- $P_o=1.0$ W (min) @ 400MHz, 28V, $P_{in}=0.1$ W



DIMENSIONS

UNIT	A	B	C	D	E	F	G	H	J	K	L
mm	9.40	8.51	6.60	1.14	12.70	0.48	1.02	0.86	2.67	2.67	5.33
	8.89	8.00	6.10	0.38		0.41	0.74	0.71	2.41	2.41	4.83
inches	0.370	0.335	0.260	0.045	0.500	0.019	0.040	0.034	0.105	0.105	0.210
	0.350	0.315	0.240	0.015		0.016	0.029	0.028	0.095	0.095	0.190

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CBO}	55	V
Collector-Emitter Voltage	V_{CEO}	30	V
Collector Current	I_c	400	mA
Emitter-Base Voltage	V_{EBO}	4	V
Collector Power Dissipation	P_{DISS}	5	W
Junction Temperature	T_J	-65 to 175	°C
Storage Temperature Range	T_{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_c=5$ mA, $I_B=0$	30	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_c=0.1$ mA, $V_{EB}=0$	55	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=0.1$ mA, $I_c=0$	4	-	-	V
Collector Cutoff Current	I_{CEO}	$V_{CE}=28$ V, $I_E=0$	-	-	20	uA
DC Current Gain	h_{FE}	$V_{CE}=5$ V, $I_c=50$ mA	25	-	200	
Current-Gain Bandwidth Product	f_T	$f=200$ MHz, $I_c=50$ mA $V_{CE}=15$ V	-	1	-	GHz
Output Capacitance	C_{ob}	$f=1.0$ MHz, $V_{CB}=30$ V	-	2.8	-	pf
Output Power	P_o	$V_{CC}=28$ V, $f=400$ MHz $P_{in}=0.1$ W	1.0	-	-	W
Collector Efficiency	η_c		45.0	-	-	%
Power Gain	G_{PE}		10	-	-	dB

Note : Above parameters , ratings , limits and conditions are subject to change.